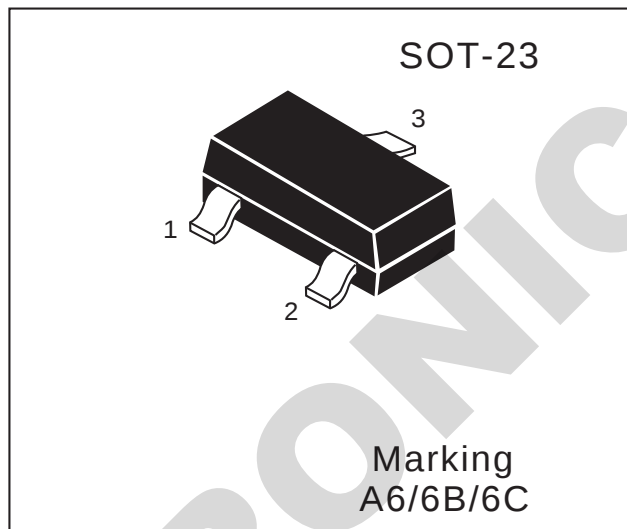


PNP EPTTAXIAL SILICON TRANSISTOR

SURFACE MOUNT SMALL
SIGANL TRANSISTORS

ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE0}	45	V
Emitter-Base Voltage	V_{CBO}	5.0	mA
Collector Current	I_C	1000	mA
Peak Colteetor Current	I_{CM}	1000	mA
Peak Fmitter Current	I_{EM}	800	mA
Power Dissipation Tsb=50°C(Note1)	P_D	310	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65~150	°C

ELECTRICAL CHARACTERISTICS

(Ta=25°C)

Charactcristic	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
DC Current Gain Current Gain Group-16	Hfe	-10		250		$V_{ce}=1.0V, I_c=100mA$
-25		160		400		
-40		250		600		
Current Gain Group-16		60				$V_{ce}=1.0V, I_c=300mA$
-25		100				
-40		170				
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.7		$I_c=500mA, I_B=50mA$
Base-Emitter Voltage	V_{bc}			1.2		$V_{ce}=1.0V, I_c=300mA$
Collector-Emitter Cutoff Current	I_{ces}			100		$V_{ce}=45V,$
				5.0		$V_{ce}=25V, T_j=150^\circ$
Emitter-Base Cutoff Current	I_{ebo}			100		$V_{eb}=4.0V$
Gain Bandwidth Product	f_T	100				$V_{ce}=5V, I_c=10mA$ $f=50MHz$
Collector-Base Capacitance	C_{cbo}			12		$V_{cb}=10V, f=1.0MHz$

Note: Device mounted on ceramic substrate 0.7mmX2.5mm² area.

DEVICE MARKING:

BC817-16=6A

BC817-25=6B

BC817-40=6C

Typical Characteristics

